2:1 Mux/Demux Analog Switches

The NLAS1053 is an advanced CMOS analog switch fabricated with silicon gate CMOS technology. It achieves very high speed propagation delays and low ON resistances while maintaining CMOS low power dissipation. The device consists of a single 2:1 Mux/Demux (SPDT), similar to ON Semiconductor's NLAS4053 analog and digital voltages that may vary across the full power supply range (from $V_{\rm CC}$ to GND).

The inhibit and select input pins have over voltage protection that allows voltages above V_{CC} up to 7.0 V to be present without damage or disruption of operation of the part, regardless of the operating voltage.

Features

- High Speed: $t_{PD} = 1$ ns (Typ) at $V_{CC} = 5.0$ V
- Low Power Dissipation: $I_{CC} = 2 \mu A \text{ (Max)}$ at $T_A = 25 \text{°C}$
- High Bandwidth, Improved Linearity, and Low RDS_{ON}
- INH Pin Allows a Both Channels 'OFF' Condition (With a High)
- RDS_{ON} \cong 25 Ω , Performance Very Similar to the NLAS4053
- Break Before Make Circuitry, Prevents Inadvertent Shorts
- Useful For Switching Video Frequencies Beyond 50 MHz
- Latchup Performance Exceeds 300 mA
- ESD Performance: HBM > 2000 V; MM > 200 V, CDM > 1500 V
- Tiny US8 Package, Only 2.1 X 3.0 mm
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

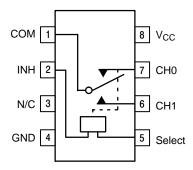


Figure 1. Pin Assignment



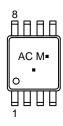
ON Semiconductor®

www.onsemi.com

MARKING DIAGRAM



US8 US SUFFIX CASE 493



AC = Specific Device Code

M = Date Code

■ = Pb–Free Package

(Note: Microdot may be in either location)

FUNCTION TABLE

INH	Select	Ch 0	Ch 1
Н	Х	OFF	OFF
L	L	ON	OFF
L	Н	OFF	ON

ORDERING INFORMATION

Device	Package	Shipping [†]
NLAS1053USG	US8 (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MAXIMUM RATINGS

	Parameter	Symbol	Value	Unit
Positive DC Supply Voltage	V _{CC}	-0.5 to +7.0	V	
Digital Input Voltage (Select a	V_{IN}	$-0.5 \le V \text{ is } \le +7.0$	V	
Analog Output Voltage (V _{CH}	or V _{COM})	V _{IS}	$-0.5 \le V \text{ is } \le V_{CC} + 0.5$	V
DC Current, Into or Out of An	y Pin	I _{IK}	50	mA
Storage Temperature Range		T _{STG}	−65 to +150	°C
Lead Temperature, 1 mm from	n Case for 10 Seconds	TL	260	°C
Junction Temperature under E	Bias	TJ	+150	°C
Thermal Resistance		θ_{JA}	250	°C/W
Power Dissipation in Still Air a	at 85°C	P_{D}	250	mW
Moisture Sensitivity		MSL	Level 1	
Flammability Rating	Oxygen Index: 30% – 35%	F _R	UL 94 V-0 @ 0.125 in	
ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	V _{ESD}	> 2000 200 N/A	٧
Latchup Performance	Above V _{CC} and Below GND at 85°C (Note 5)	I _{Latchup}	±300	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2-ounce copper trace with no air flow.
- 2. Tested to EIA/JESD22-A114-A.
- 3. Tested to EIA/JESD22-A115-A.
- 4. Tested to JESD22-C101-A.
- 5. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Characteristics	Symbol	Min	Max	Unit	
Positive DC Supply Voltage		V _{CC}	2.0	5.5	V
Digital Input Voltage (Select and Inhibit)		V _{IN}	GND	5.5	V
Static or Dynamic Voltage Across an Off Switch		V _{IO}	GND	V _{CC}	V
Analog Input Voltage (CH, COM)		V _{IS}	GND	V _{CC}	V
Operating Temperature Range, All Package Types		T _A	-55	+125	°C
Input Rise or Fall Time (Enable Input)	$V_{cc} = 3.3 \text{ V} \pm 0.3 \text{ V}$ $V_{cc} = 5.0 \text{ V} \pm 0.5 \text{ V}$	t _r , t _f	0	100 20	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

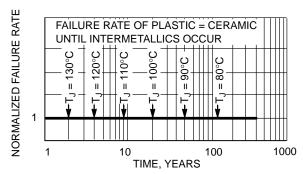


Figure 2. Failure Rate versus Time Junction Temperature

DC CHARACTERISTICS - Digital Section (Voltages Referenced to GND)

				Guaranteed Limit			
Parameter	Condition	Symbol	V _{CC}	-55°C to 25°C	<85°C	<125°C	Unit
Minimum High-Level Input Voltage, Select and Inhibit Inputs		V _{IH}	2.0 2.5 3.0 4.5 5.5	1.5 1.9 2.1 3.15 3.85	1.5 1.9 2.1 3.15 3.85	1.5 1.9 2.1 3.15 3.85	V
Maximum Low-Level Input Voltage, Select and Inhibit Inputs		V _{IL}	2.0 2.5 3.0 4.5 5.5	0.5 0.6 0.9 1.35 1.65	0.5 0.6 0.9 1.35 1.65	0.5 0.6 0.9 1.35 1.65	V
Maximum Input Leakage Current, Select and Inhibit Inputs	V _{IN} = 5.5 V or GND	I _{IN}	0 V to 5.5 V	± 0.1	±1.0	±1.0	μΑ
Maximum Quiescent Supply Current	Select and Inhibit = V _{CC} or GND	Icc	5.5	1.0	1.0	2.0	μΑ

DC ELECTRICAL CHARACTERISTICS - Analog Section

				Guara	nteed Limit	İ	
Parameter	Condition	Symbol	V _{CC}	-55 to 25°C	< 85°C	< 125°C	Unit
Maximum "ON" Resistance (Figures 17 – 23)	$\begin{aligned} &V_{IN} = V_{IL} \text{ or } V_{IH} \\ &V_{IS} = \text{GND to } V_{CC} \\ &I_{IN}I \leq 10.0 \text{ mA} \end{aligned}$	R _{ON}	2.5 3.0 4.5 5.5	70 40 20 16	85 46 28 22	105 52 34 28	Ω
ON Resistance Flatness (Figures 17 – 23)	$\begin{aligned} &V_{IN} = V_{IL} \text{ or } V_{IH} \\ &I_{IN}I \leq 10.0 \text{ mA} \\ &V_{IS} = 1V, 2V, 3.5V \end{aligned}$	R _{FLAT} (ON)	4.5	4	4	5	Ω
ON Resistance Match Between Channels	$\begin{aligned} &V_{IN} = V_{IL} \text{ or } V_{IH} \\ &I_{IN}I \leq 10.0 \text{ mA} \\ &V_{CH1} \text{ or } V_{CH0} = 3.5 \text{ V} \end{aligned}$	ΔR _{ON} (ON)	4.5	2	2	3	Ω
CH1 or CH0 Off Leakage Current (Figure 9)	$V_{IN} = V_{IL} \text{ or } V_{IH}$ $V_{CH1} \text{ or } V_{CH0} = 1.0 V_{COM} 4.5 V$	I _{CH0} I _{CH1}	5.5	1	10	100	nA
COM ON Leakage Current (Figure 9)	$\begin{aligned} &V_{IN} = V_{IL} \text{ or } V_{IH} \\ &V_{CH1} \text{ 1.0 V or 4.5 V with } V_{CH0} \\ &\text{floating or} \\ &V_{CH1} \text{ 1.0 V or 4.5 V with } V_{CH1} \\ &\text{floating} \\ &V_{COM} = 1.0 \text{ V or 4.5 V} \end{aligned}$	I _{COM(ON)}	5.5	1	10	100	nA

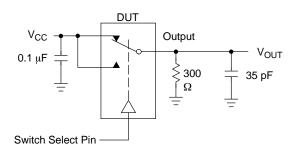
AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ ns}$)

				Guaranteed Max Limit							
			v _{cc}	-55 to 25°C < 85°C		< 12	25°C				
Parameter	Test Conditions	Symbol	(V)	Min	Тур*	Max	Min	Max	Min	Max	Unit
Turn-On Time (Figures 12 and 13) INH to Output	$R_L = 300 \Omega$, $C_L = 35 pF$ (Figures 4 and 5)	t _{ON}	2.5 3.0 4.5 5.5	2 2 1 1	7 5 4 3	12 10 9 8	2 2 1 1	15 15 12 12	2 2 1 1	15 15 12 12	ns
Turn-Off Time (Figures 12 and 13) INH to Output	$R_L = 300 \Omega$, $C_L = 35 pF$ (Figures 4 and 5)	^t OFF	2.5 3.0 4.5 5.5	2 2 1 1	7 5 4 3	12 10 9 8	2 2 1 1	15 15 12 12	2 2 1 1	15 15 12 12	ns
Transition Time (Channel Selection Time) (Figure) Select to Output	$R_L = 300 \Omega$, $C_L = 35 pF$ (Figures and)	t _{trans}	2.5 3.0 4.5 5.5	5 5 2 2	18 13 12 9	28 21 16 14	5 5 2 2	30 25 20 20	5 5 2 2	30 25 20 20	ns
Minimum Break-Before-Make Time	$V_{IS} = 3.0 \text{ V (Figure 3)}$ $R_L = 300 \Omega$, $C_L = 35 \text{ pF}$	t _{BBM}	2.5 3.0 4.5 5.5	1 1 1	12 11 6 5		1 1 1		1 1 1		ns
			Typical @ 25, VCC = 5.0 V								
Maximum Input Capacitance, Select/INH Input Analog I/O (switch off) Common I/O (switch off) Feedthrough (switch on)		C _{IN} C _{NO} or C _{NC} C _{COM} C _(ON)	8 10 10 20					pF			

^{*}Typical Characteristics are at 25°C.

ADDITIONAL APPLICATION CHARACTERISTICS (Voltages Referenced to GND Unless Noted)

			V _{CC}	Typical	
Parameter	Condition	Symbol	V	25°C	Unit
Maximum On–Channel –3dB Bandwidth or Minimum Frequency Response (Figure 10)	V_{IN} = 0 dBm V_{IN} centered between V_{CC} and GND (Figure 7)	BW	3.0 4.5 5.5	170 200 200	MHz
Maximum Feedthrough On Loss	V _{IN} = 0 dBm @ 100 kHz to 50 MHz V _{IN} centered between V _{CC} and GND (Figure 7)	V _{ONL}	3.0 4.5 5.5	-3 -3 -3	dB
Off-Channel Isolation (Figure 10)	$ f = 100 \text{ kHz; } V_{\text{IS}} = 1 \text{ V RMS} $ V_{IN} centered between V_{CC} and GND (Figure 7)	V _{ISO}	3.0 4.5 5.5	-93 -93 -93	dB
Charge Injection Select Input to Common I/O (Figure 15)	$\begin{aligned} &V_{IN} = V_{CC\ to}\ GND,\ F_{IS} = 20\ kHz\\ &t_r = t_f = 3\ ns\\ &R_{IS} = 0\ \Omega,\ C_L = 1000\ pF\\ &Q = C_L * \Delta V_{OUT}\\ &(Figure\ 8) \end{aligned}$	Q	3.0 5.5	1.5 3.0	рС
Total Harmonic Distortion THD + Noise (Figure 14)	F_{IS} = 20 Hz to 100 kHz, RL = Rgen = 600 Ω C_L = 50 pF V_{IS} = 5.0 V_{PP} sine wave	THD	5.5	0.1	%



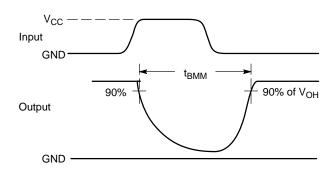
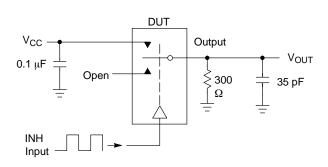


Figure 3. t_{BBM} (Time Break-Before-Make)



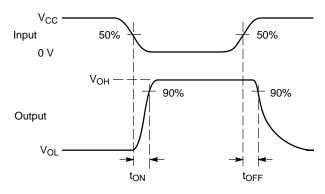
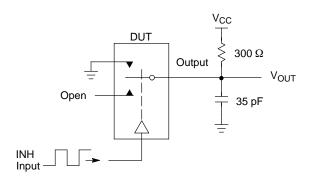


Figure 4. t_{ON}/t_{OFF}



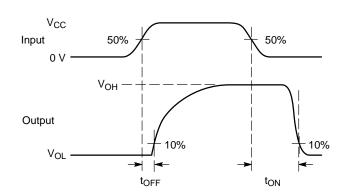


Figure 5. t_{ON}/t_{OFF}

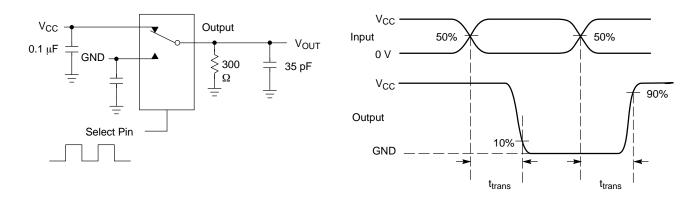
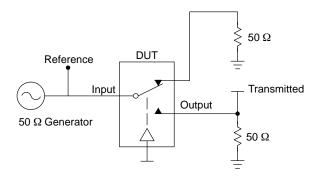


Figure 6. t_{trans} (Channel Selection Time)



Channel switch control/s test socket is normalized. Off isolation is measured across an off channel. On loss is the bandwidth of an On switch. V_{ISO} , Bandwidth and V_{ONL} are independent of the input signal direction.

$$\begin{split} &V_{ISO} = \text{Off Channel Isolation} = 20 \text{ Log } \left(\frac{\text{VOUT}}{\text{V}_{IN}} \right) \text{ for V}_{IN} \text{ at 100 kHz} \\ &V_{ONL} = \text{On Channel Loss} = 20 \text{ Log } \left(\frac{\text{VOUT}}{\text{V}_{IN}} \right) \text{ for V}_{IN} \text{ at 100 kHz to 50 MHz} \end{split}$$

Bandwidth (BW) = the frequency 3 dB below V_{ONL}

Figure 7. Off Channel Isolation/On Channel Loss (BW)/Crosstalk (On Channel to Off Channel)/V_{ONL}

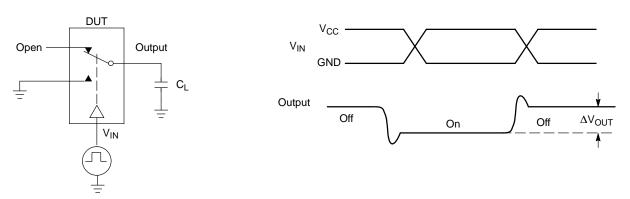
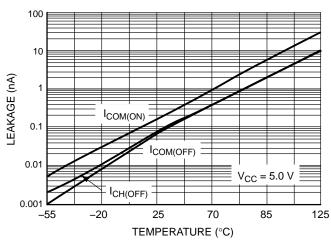


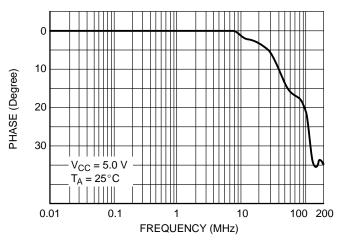
Figure 8. Charge Injection: (Q)



0 Bandwidth (ON-RESPONSE)
-40 Off Isolation
-60 V_{CC} = 5.0 V
T_A = 25°C
-100 0.01 0.1 1 10 100 200
FREQUENCY (MHz)

Figure 9. Switch Leakage versus Temperature

Figure 10. Bandwidth and Off-Channel Isolation



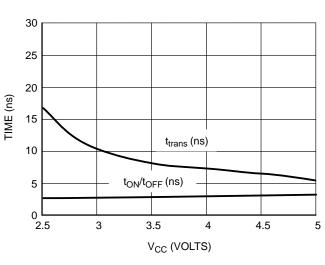
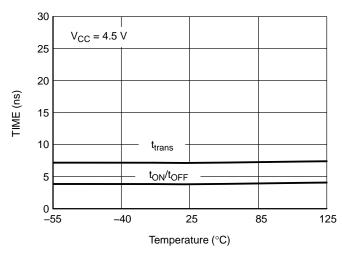


Figure 11. Phase versus Frequency

Figure 12. $t_{\mbox{\scriptsize ON}}$ and $t_{\mbox{\scriptsize OFF}}$ versus $V_{\mbox{\scriptsize CC}}$ at 25°C



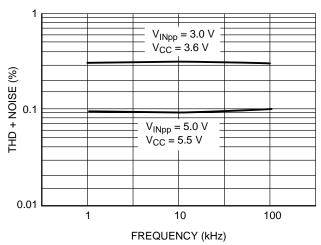


Figure 13. t_{ON} and t_{OFF} versus Temp

Figure 14. Total Harmonic Distortion Plus Noise versus Frequency

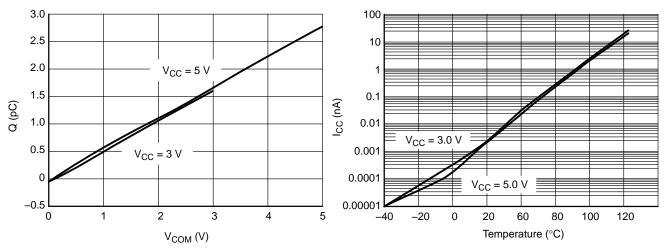


Figure 15. Charge Injection versus COM Voltage

Figure 16. I_{CC} versus Temp, V_{CC} = 3 V & 5 V

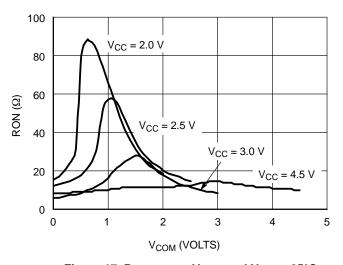


Figure 17. R_{ON} versus V_{COM} and V_{CC (@} 25°C

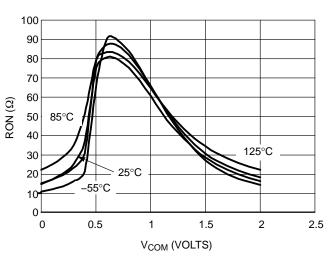


Figure 18. R_{ON} versus V_{COM} and Temperature, $V_{CC}\,2.0\;V$

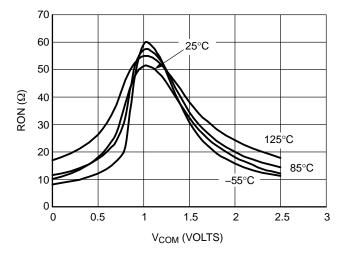


Figure 19. R_{ON} versus V_{COM} and Temperature, V_{CC} = 2.5 V

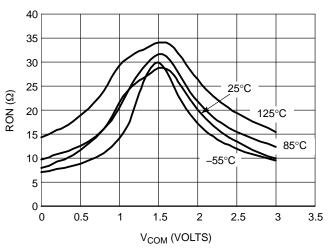
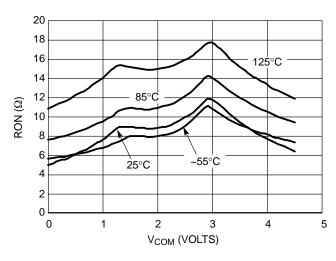


Figure 20. R_{ON} versus V_{COM} and Temperature, V_{CC} = 3.0 V



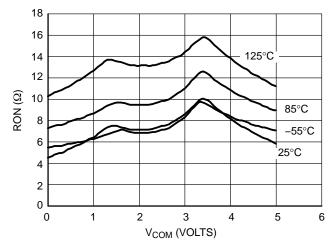


Figure 21. R_{ON} versus V_{COM} and Temperature, V_{CC} = 4.5 V

Figure 22. R_{ON} versus V_{COM} and Temperature, V_{CC} = 5.0 V

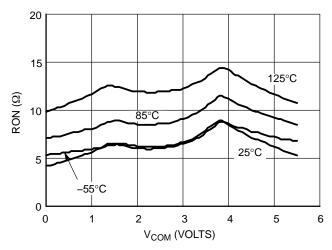
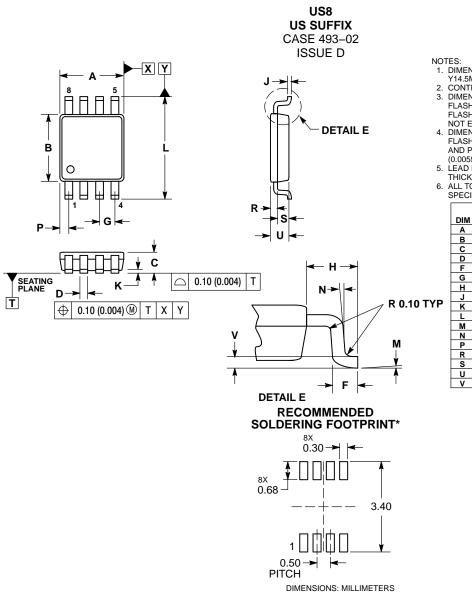


Figure 23. R_{ON} versus V_{COM} and Temperature, V_{CC} = 5.5 V

PACKAGE DIMENSIONS



- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSION OR GATE BURR. MOLD
- FLASH, PROTRUSION AND GATE BURR SHALL NOT EXCEED 0.14MM (0.0055") PER SIDE.
 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH
- AND PROTRUSION SHALL NOT EXCEED 0.14MM (0.0055") PER SIDE.
 5. LEAD FINISH IS SOLDER PLATING WITH THICKNESS OF 0.0076-0.0203MM (0.003-0.008").
- ALL TOLERANCE UNLESS OTHERWISE SPECIFIED ±0.0508MM (0.0002").

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	1.90	2.10	0.075	0.083
В	2.20	2.40	0.087	0.094
C	0.60	0.90	0.024	0.035
D	0.17	0.25	0.007	0.010
F	0.20	0.35	0.008	0.014
G	0.50	BSC	0.020	BSC
Н	0.40	REF	0.016	REF
J	0.10	0.18	0.004	0.007
K	0.00	0.10	0.000	0.004
L	3.00	3.20	0.118	0.128
М	0 °	6°	0°	6°
N	0 °	10 °	0°	10 °
Р	0.23	0.34	0.010	0.013
R	0.23	0.33	0.009	0.013
S	0.37	0.47	0.015	0.019
U	0.60	0.80	0.024	0.031
٧	0.12	BSC	0.005	BSC

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and the are registered trademarks of Semiconductor Components Industries, LLC (SCILLC) or its subsidiaries in the United States and/or other countries. SCILLC owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of SCILLC's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA **Phone**: 303–675–2175 or 800–344–3860 Toll Free USA/Canada

Fax: 303-675-2175 of 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada

Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910 Japan Customer Focus Center

Japan Customer Focus Cente Phone: 81–3–5817–1050 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

ON Semiconductor: